

P-Channel 30 V (D-S) MOSFET

MOSFET PRODUCT SUMMARY

V _{DS} (V)	R _{DS(on)} (mΩ)(TYP.)	I _D (A) ^a	Q _g (Typ.)
- 30	53 at V _{GS} = - 10 V	- 4	16 nC
	68 at V _{GS} = - 4.5		

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested

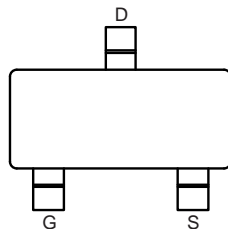
APPLICATIONS

- Load Switch
- Notebook Adaptor Switch
- DC/DC Converter
- Power Management

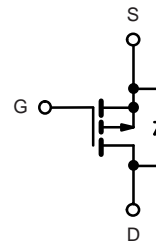


RoHS
COMPLIANT

SOT-23 Pin Configuration



Top View



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	- 30	V
Gate-Source Voltage	V _{GS}	± 20	
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _C = 25 °C	- 4
		T _C = 100 °C	- 2.4
Pulsed Drain Current ^b	I _{DM}	- 20	A
Maximum Power Dissipation ^c	P _D	T _C = 25 °C	1.7
		T _C = 100 °C	0.68
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	MAX	UNIT
Junction-to-Ambient	R _{thJA}	140	°C/W
Junction-to-Case	R _{thJC}	73.5	

Notes

- Calculated continuous current based on maximum allowable junction temperature.
- Repetitive rating; pulse width limited by max. junction temperature.
- P_d is based on max. junction temperature, using junction-case thermal resistance.
- The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.

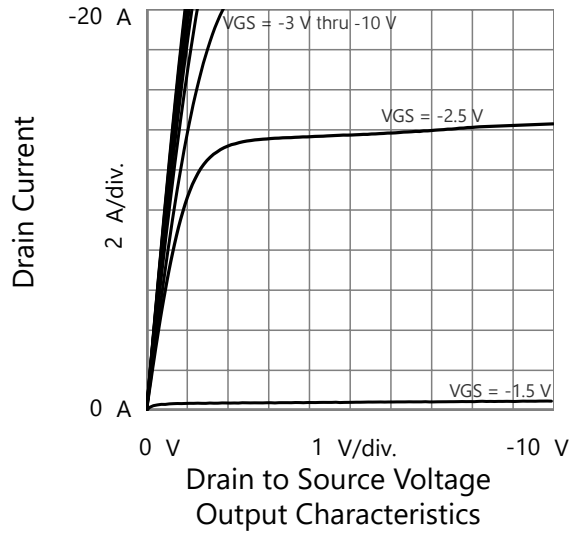
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-30			V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.5		-1.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	-4			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -3.8\text{ A}$		53	59	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -3\text{ A}$		68	80	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -3.8\text{ A}$		22		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		789		pF
Output Capacitance	C_{oss}			68		
Reverse Transfer Capacitance	C_{rss}			61		
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -3.8\text{ A}$		16		nC
Gate-Source Charge	Q_{gs}			1.8		
Gate-Drain Charge	Q_{gd}			3		
Gate Resistance	R_g	$f = 1\text{ MHz}$		8		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, I_D = -3.8\text{ A},$ $V_{GEN} = -10\text{ V}, R_g = 3\text{ }\Omega$		7.5		ns
Rise Time	t_r			5		
Turn-Off Delay Time	$t_{d(off)}$			45		
Fall Time	t_f			11		
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-4	A
Pulse Diode Forward Current ^a	I_{SM}				-20	
Body Diode Voltage	V_{SD}	$I_S = -1\text{ A}$			-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		13		ns
Body Diode Reverse Recovery Charge	Q_{rr}				4.5	

Notes:

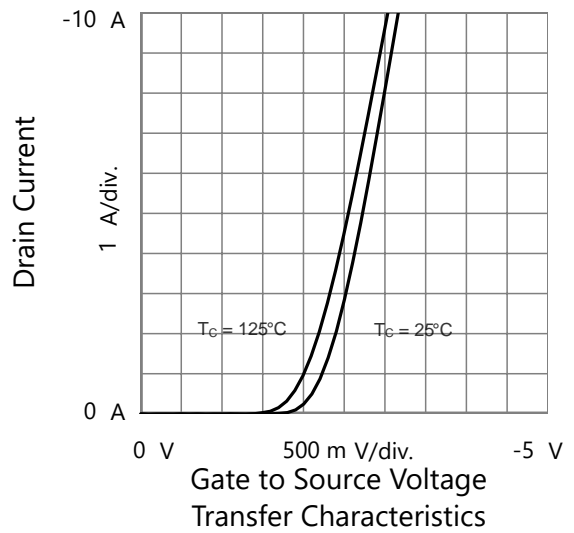
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

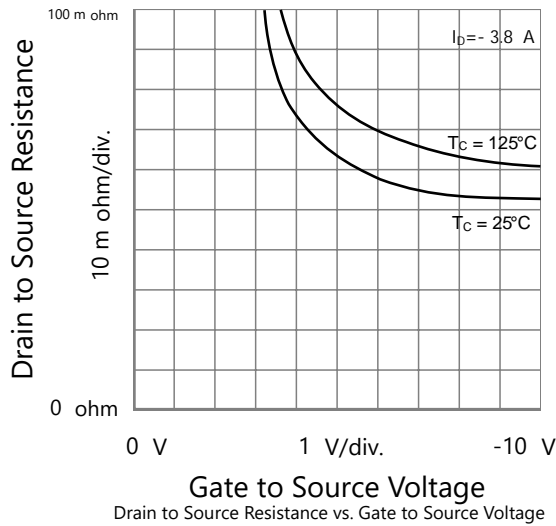
TYPICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise noted)



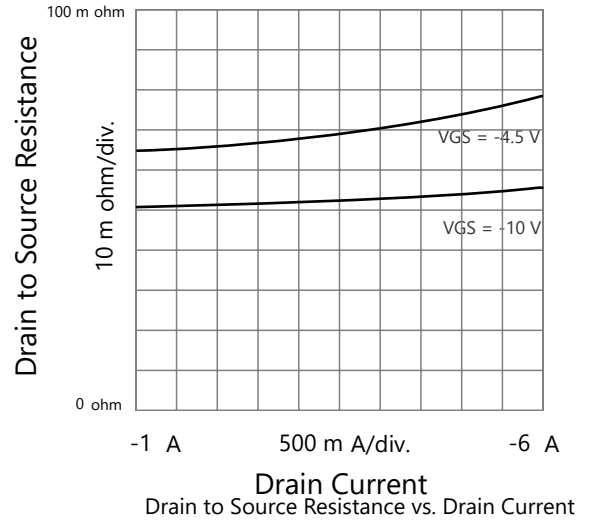
Drain to Source Voltage
Output Characteristics



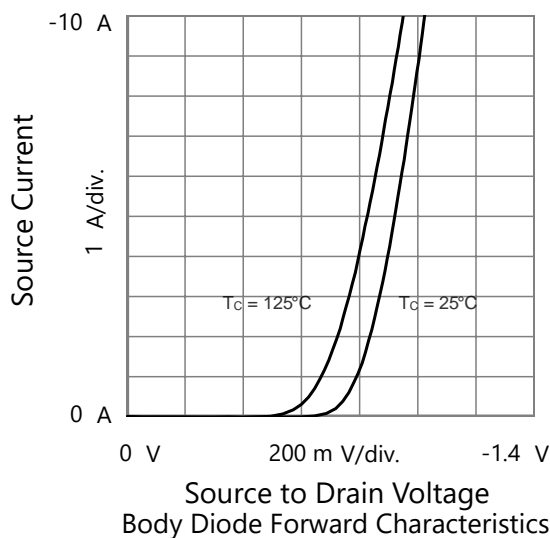
Gate to Source Voltage
Transfer Characteristics



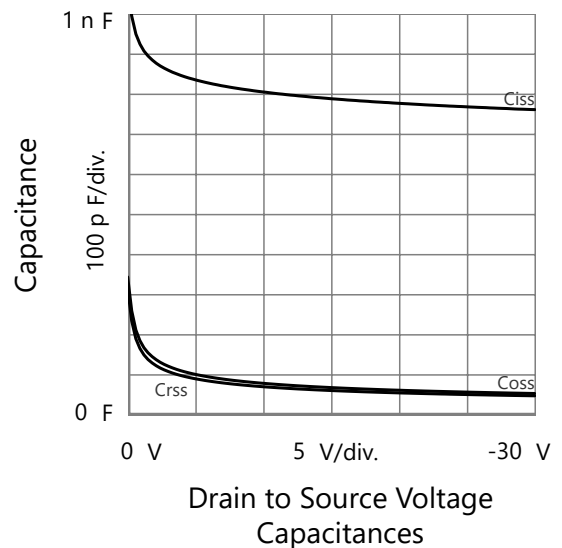
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



Drain Current
Drain to Source Resistance vs. Drain Current

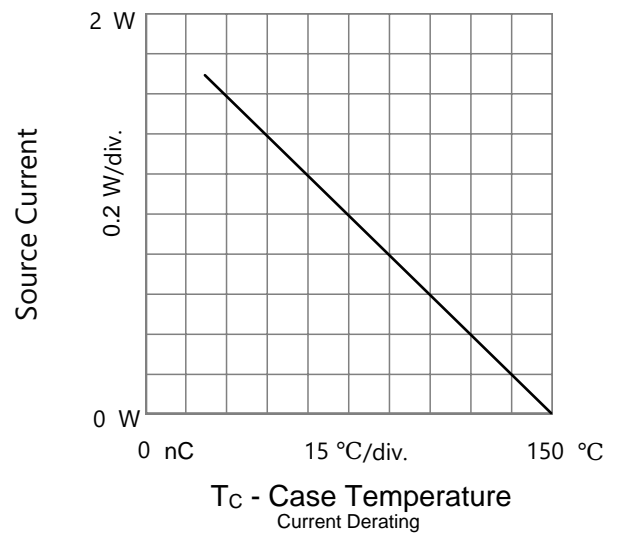
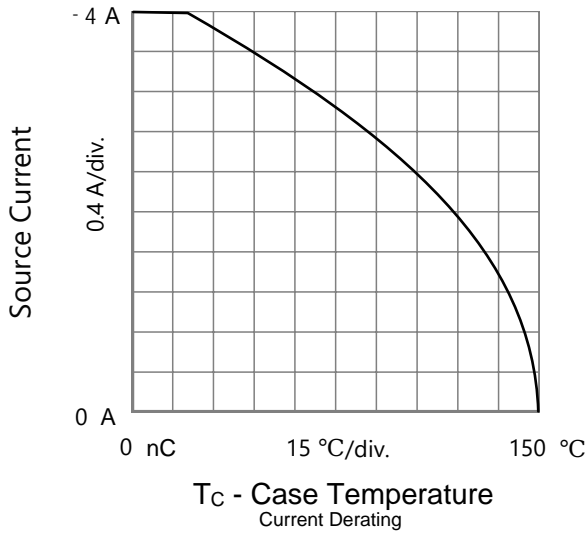
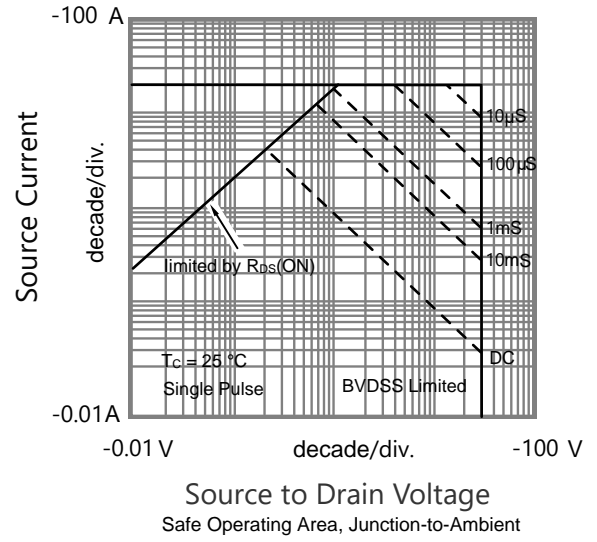
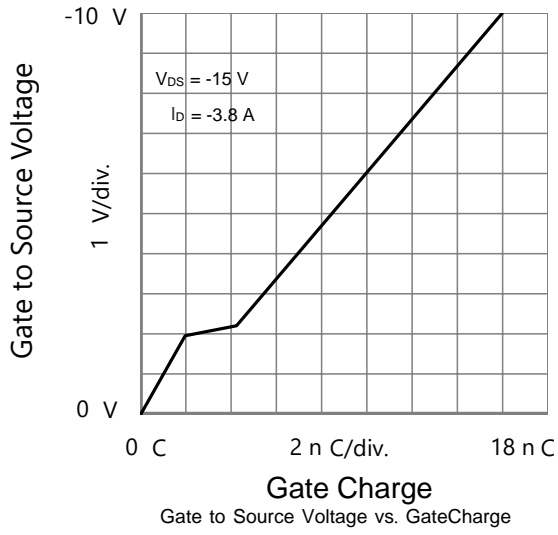


Source to Drain Voltage
Body Diode Forward Characteristics

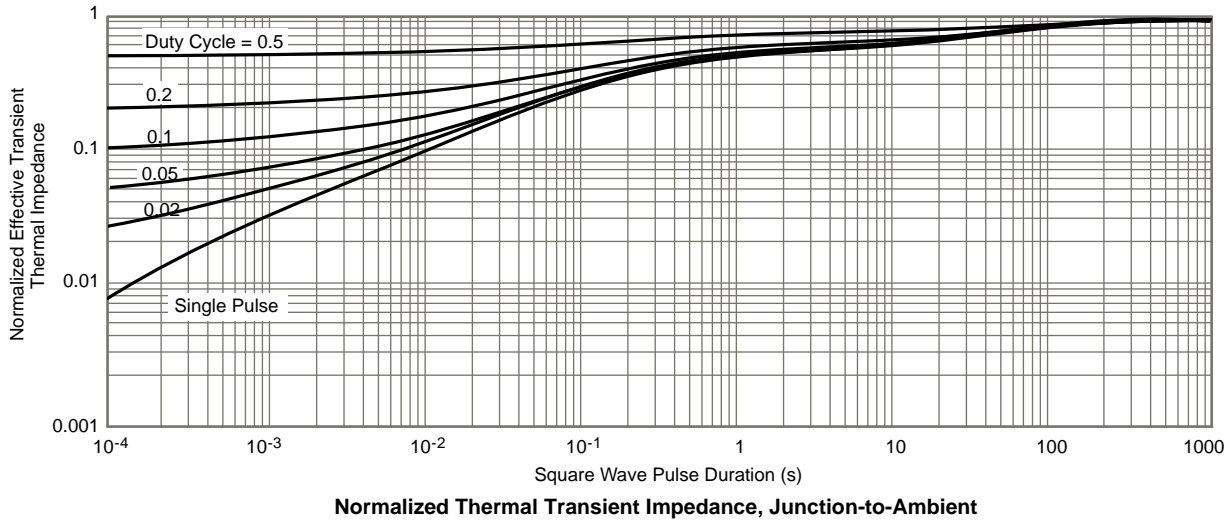


Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)



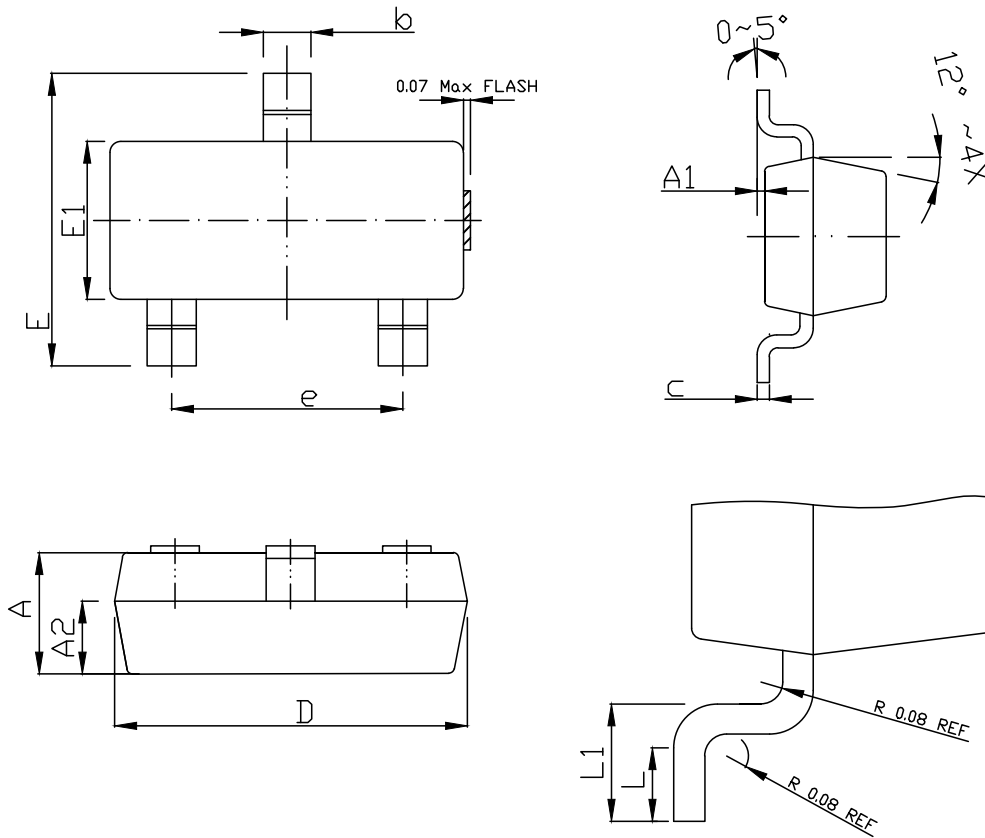
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)
 are given for general guidelines only to enable the user to get a “ball park” indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23 PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.80	1.00	1.30
A1	0.00	0.05	0.15
b	0.25	0.40	0.55
c	0.11 BSC		
D	2.60	2.90	3.20
E	2.10	2.40	2.70
E1	1.10	1.30	1.48
e	1.90 BSC		
L	0.17	-	-
L1	0.28	0.40	0.53
A2	0.60 REF		

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